

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30889	(first near conductivity near type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:43
L2	7774	(first near conductivity near type) and (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:43
L3	6669	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:43
L4	310	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44
L5	0	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44
L6	223	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44
L7	192	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction and concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44
L8	190	(first near conductivity near type) and (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44

L9	120	(first near conductivity near type) same (semiconductor adj layer) and (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:44
L10	109	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) and (insulating or dielectric) and (control adj electrode) and junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:45
L11	55	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) and (control adj electrode) and junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:45
L12	40	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) same (control adj electrode) and junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:45
L13	12	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) same (control adj electrode) same junction and concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:45
L14	6	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) same (control adj electrode) same junction same concentration and region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:45
L15	6	(first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) same (control adj electrode) same junction same concentration same region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:49

L16	23	"5648671"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:47
L17	3	((first near conductivity near type) same (semiconductor adj layer) same (second near conductivity near type) same (insulating or dielectric) same (control adj electrode) same junction same concentration same region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:49